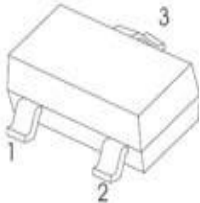
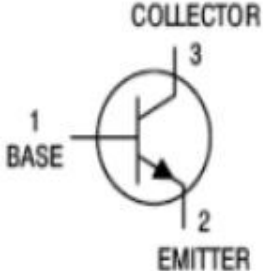


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors		
<p style="text-align: center;"><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p style="text-align: center;">Marking :J8</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>• AM/FM Amplifier, Local Oscillator of FM/VHF Tuner</li> <li>• High Current Gain Bandwidth Product</li> </ul>		
<b>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</b>			
<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Collector-Base Voltage	VCBO	30	V
Collector-Emitter Voltage	VCEO	15	V
Emitter-Base Voltage	VEBO	5	V
Collector Current -Continuous	IC	50	mA
Collector Current -Pulsed	ICM	300	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

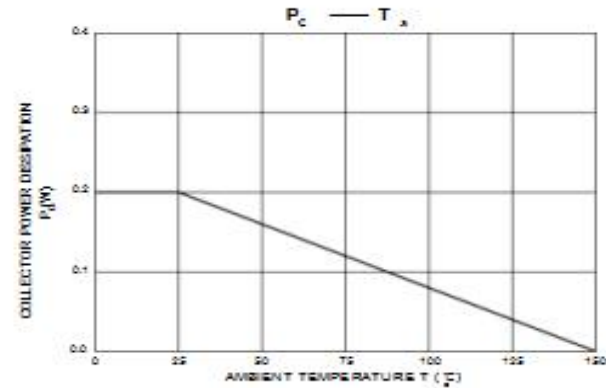
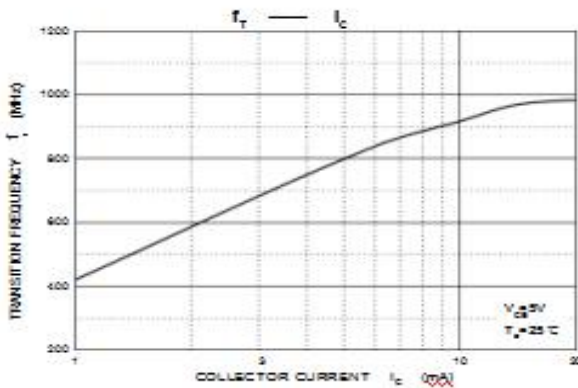
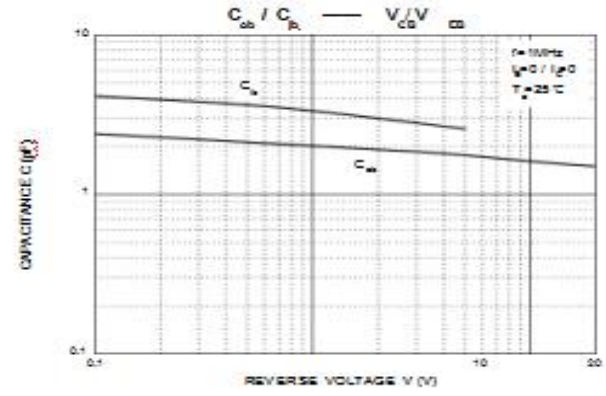
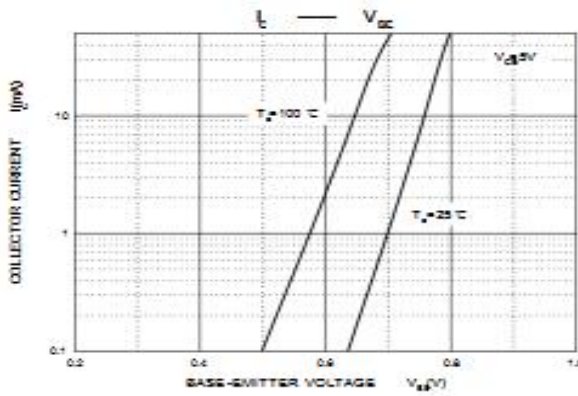
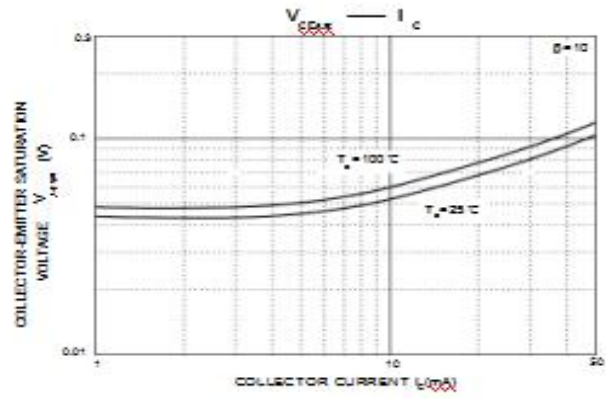
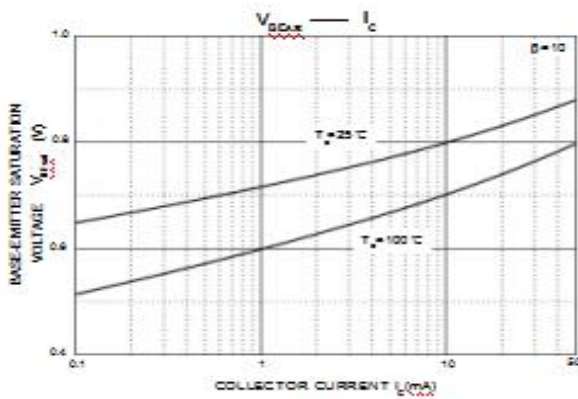
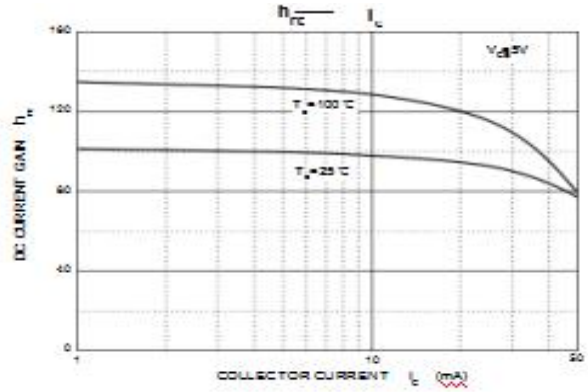
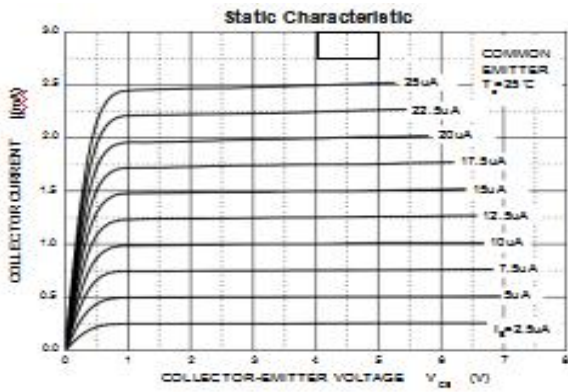
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	30			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	15			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current	ICBO	VCB= 20 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCB= 15V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 3V , IC=0			0.1	μA
DC current gain	hFE	VCE= 5V, IC= 10mA	50			
	hFE	VCE= 5V, IC= 1mA	70		200	
Collector-emitter saturation voltage	VCE(sat)	IC= 10mA, IB= 1mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= 10 mA, IB= 1mA			1	V
Transition frequency	fT	VCE= 5V, IC= 5mA f=400MHz	50			MHz

**CLASSIFICATION OF hFI**

Rank	L	H
Range	50-100	100-200

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)